DBD10G

1.0A Single-Phase Bridge Rectifier

ON Semiconductor®

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Features

- Plastic molded structure
- Peak reverse voltage: V_{RM}=600V
- Average output current : I_O=1.0A

## SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	600	V
Average Output Current Ta = 25°C	I_O	1.0	A
Surge Forward Current 50Hz sine wave, 1cycle	I_{FSM}	30	A
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	−40 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

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ELECTRICAL CONNECTION
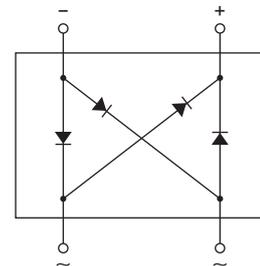
MARKING
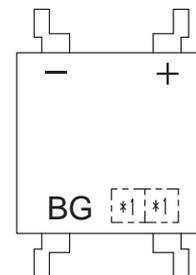
✳1 : Lot No.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet

February 2016 - Rev. 1

Publication Order Number :
DBD10G/D

DBD10G

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Forward Voltage	V_F	$I_F = 0.5A$			1.05	V
Reverse Current	I_R	$V_R = V_{RM}$			10	µA
Thermal Resistance	Rth(j-l)	Junction-Lead			15	°C / W
	Rth(j-a)	Junction-Ambient			68	°C / W

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$I_F - V_F$

IT03617

$I_O - Ta$

IT03618

$I_{FSM} - n$

IT03619

$P_F - I_O$

IT03620
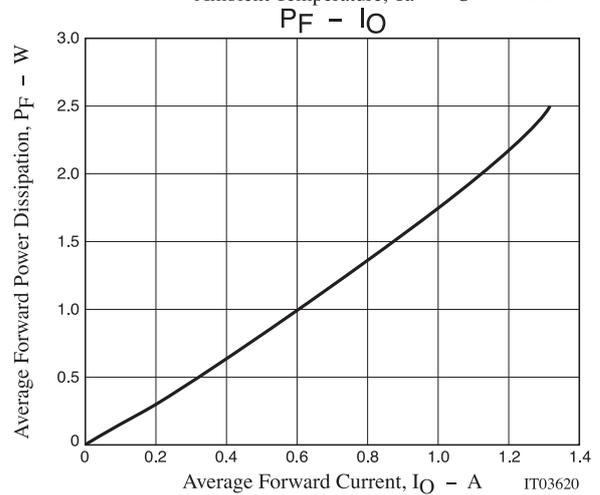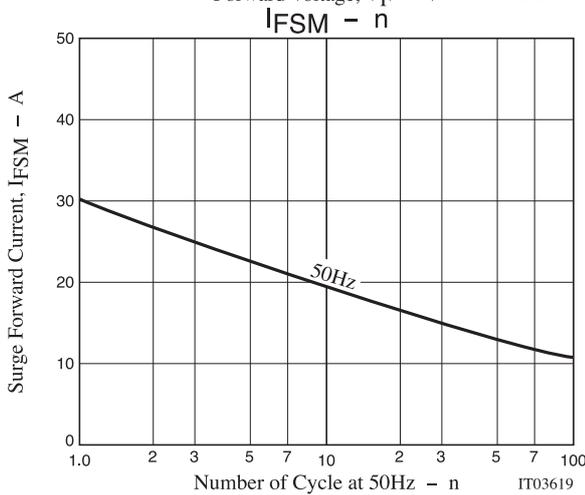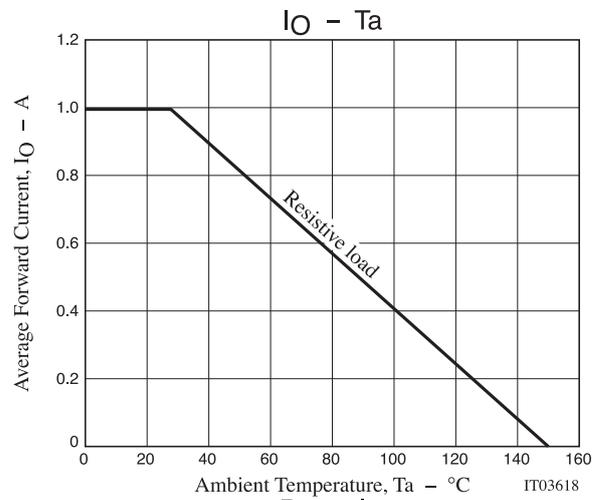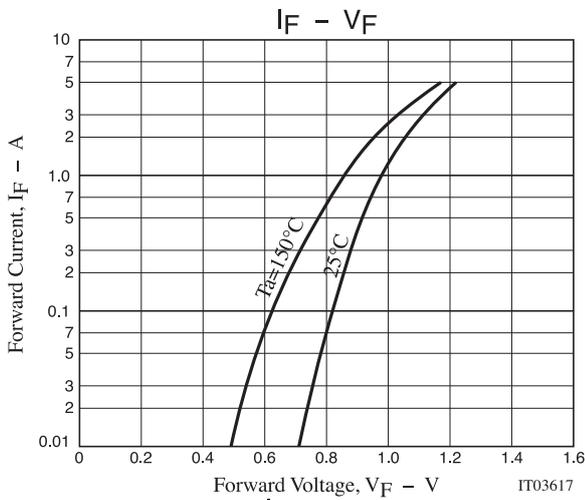
DBD10G

PACKAGE DIMENSIONS

unit : mm

DBD10G-TM-E

PDIP4 GW 6.8x6.5
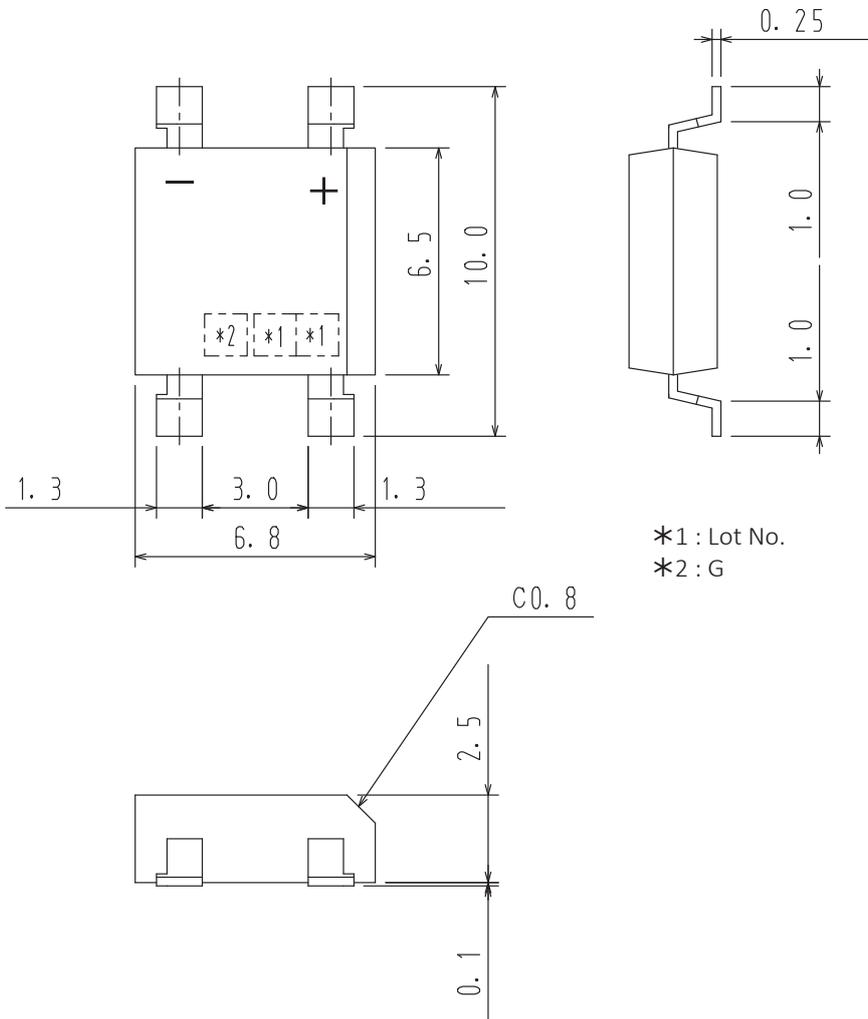
∗1 : Lot No.

∗2 : G

DBD10G

PACKAGE DIMENSIONS
unit : mm

DBD10G-E

PDIP4 6.8x6.5, 5.0P / DBD10

6.5

6.8

− +

*2 *1 *1

MAX15°

7.62

MAX15°

0.25

C0.8

2.5

3.7MAX

3.2

0.55

5.0

✳1 : Lot No.
✳2 : G

DBD10G